

In the Claims:

1. (Currently Amended) A method of patterning metal layers of a semiconductor wafer, the method comprising:

depositing a first conductive layer over a substrate;

depositing an insulating layer over the first conductive layer;

depositing a second conductive layer over the insulating layer;

depositing a first layer of resist over the second conductive layer;

patterned the first layer of resist with a first pattern;

developing said patterned first layer of resist;

removing portions of said first layer of resist according to said first pattern to expose portions of said second conductive layer;

depositing a second layer of resist over remaining portions of the first layer of resist and exposed portions of said second conductive layer;

patterned the second layer of resist with a second pattern; and

developing said patterned second layer of resist;

stripping portions of said second layer of resist according to said second pattern; and

simultaneously transferring etching the first pattern to the first conductive layer according to the first pattern and the second pattern to the second conductive layer according to the second pattern in a single etching process.

2. (Currently Amended) The method according to Claim 1 wherein the single etching process transferring the first and second patterns comprise comprises exposing the wafer to a single reactive ion etch process.

3. (Original) The method according to Claim 1 wherein the first resist comprises a negative resist and the second resist comprises a positive resist.

4. (Original) The method according to Claim 1 wherein the first resist comprises a positive resist and the second resist comprises a negative resist.

5. (Currently Amended) The method according to Claim 1 wherein the insulating layer comprises a capacitor dielectric, wherein etching transferring the first pattern to the first conductive layer comprises forming bottom metal plates of a MIM capacitor, and wherein etching transferring the second pattern to the second conductive layer comprises forming top metal plates of the MIM capacitor.

6. (Currently Amended) The method according to Claim 1 further comprising etching transferring the first pattern to the insulating layer according to the first pattern.

7. (Currently Amended) A method of patterning metal layers of a semiconductor wafer, the wafer comprising a first conductive layer, an insulating layer disposed over the first conductive layer and a second conductive layer disposed over the insulating layer, the method comprising:
depositing a first layer of resist over the second conductive layer;
patterned the first layer of resist with a first pattern;
developing said patterned first layer of resist;

removing portions of said first layer of resist according to said first pattern to expose portions of said second conductive layer;

depositing a second layer of resist over remaining portions of the first layer of resist and exposed portions of said second conductive layer;

patterning the second layer of resist with a second pattern;

developing said patterned second layer of resist;

stripping portions of said second layer of resist according to said second pattern; and

simultaneously transferring etching the first pattern to the first conductive layer according to the first pattern and transferring the second pattern to the second conductive layer according to the second pattern in a single etching process.

8. (Currently Amended) The method according to Claim 7 wherein the single etching process transferring the first and second patterns comprise comprises exposing the wafer to a reactive ion etch process.

9. (Original) The method according to Claim 8 wherein the first resist comprises a negative resist and the second resist comprises a positive resist.

10. (Original) The method according to Claim 8 wherein the first resist comprises a positive resist and the second resist comprises a negative resist.

11. (Currently Amended) The method according to Claim 8 wherein the insulating layer comprises a capacitor dielectric, wherein etching transferring the first pattern to the first

conductive layer comprises forming bottom metal plates of a MIM capacitor, and wherein
~~etching transferring the second pattern to the second conductive layer~~ comprises forming top
metal plates of the MIM capacitor.

12. (Currently Amended) The method according to Claim 7 further comprising ~~etching~~
~~transferring the first pattern to the insulating layer according to the first pattern.~~

13. (Currently Amended) A method of forming capacitive plates of a MIM capacitor,
comprising:

providing a wafer having a substrate;
depositing a first conductive layer on the substrate;
depositing a capacitor dielectric layer over the first conductive layer;
depositing a second conductive layer over the capacitor dielectric layer;
depositing a first layer of resist over the second conductive layer;
patterned the first layer of resist with a first pattern;
developing said patterned first layer of resist;
removing portions of said first layer of resist according to said first pattern to expose
portions of said second conductive layer;
depositing a second layer of resist over remaining portions of the first layer of resist and
exposed portions of said second conductive layer;
patterned the second resist with a second pattern; and
developing said patterned second layer of resist;
stripping portions of said second layer of resist according to said second pattern; and

~~simultaneously transferring the first pattern to etching the first conductive layer according to the first pattern and transferring the second pattern to the second conductive layer according to the second pattern in a single etching process.~~

14. (Currently Amended) The method according to Claim 13 wherein ~~the single etching process transferring the first and second patterns comprise comprises~~ exposing the wafer to a reactive ion etch process.

15. (Original) The method according to Claim 13 wherein the first resist comprises a negative resist and the second resist comprises a positive resist.

16. (Original) The method according to Claim 13 wherein the first resist comprises a positive resist and the second resist comprises a negative resist.

17. (Currently Amended) The method according to Claim 13 further comprising etching transferring the first pattern to the insulating layer according to the first portion.

18. (New) The method according to Claim 1 wherein said step of patterning the first layer of resist comprises the step of patterning with a lithographic process.

19. (New) The method according to Claim 18 wherein said step of patterning the second layer of resist comprises the step of patterning with a lithographic process.